

[1] 100% [2] 100% [3] 100% [4] 100%

 Drafts Pending Active

- L1: ((3) ("6,204,139") or ("6,249,014") or ("6,249,015"))
- L2: (424386) RAM or memory.clm.
- L3: (1427) 2 and ((top or upper) adj electrode)
- L4: (1220) 3 and ((bottom or lower) adj electrode)
- L5: ((13) 4 and (width or area) near10 ((non adj uniform2) or equal or unequal))

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US	INPT	P	Document ID	Issue Date	Pages	Title	Current CN	Current KB	Retrieved	Inventor	S	C	R	M	I	
36	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20010920	20010920	Semiconductor device having ferroelectric cap	257/295	257/E21.01		Kanaya, Hiroyuki et al.	<input checked="" type="checkbox"/>					
37	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6809401	20041026	Memory, writing apparatus, reading appa	257/613			Nishihara, Takashi et al.	<input checked="" type="checkbox"/>					
38	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6809360	20041026	Semiconductor device and method of manufac	257/295	257/296; 257/310;		Kato, Yoshikazu	<input checked="" type="checkbox"/>					
39	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6798006	20040928	27	Semiconductor device and manufacturing metho	257/296	257/300; 257/304;		Amo, Atsushi et al.	<input checked="" type="checkbox"/>				
40	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6797978	20040928	13	Method for fabricating an array of ultra-small	257/3	257/5; 257/774		Gonzalez, Fernando N. M. et al.	<input checked="" type="checkbox"/>				
41	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6762065	20040713	59	Semiconductor device having ferroelectric ca	438/3			Kanaya, Hiroyuki et al.	<input checked="" type="checkbox"/>				
42	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6753565	20040622	61	Container capacitor array having a common t	257/306	257/309; 257/E21.01		Durcan, D. Mark et al.	<input checked="" type="checkbox"/>				
43	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6693319	20040217	61	Container capacitor structure and method of	257/308	257/311; 257/E21.01		Durcan, D. Mark et al.	<input checked="" type="checkbox"/>				
44	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6690050	20040210	68	Semiconductor device and method of manufac	257/296	257/306; 257/310;		Taniguchi, Toshio et al.	<input checked="" type="checkbox"/>				
45	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6680499	20040120	33	Semiconductor device and method of manufac	257/295	257/E21.66; 4;		Kumura, Yoshinori et al.	<input checked="" type="checkbox"/>				
46	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6627497	20030930	61	Semiconductor integrated circuit devi	438/253	257/E21.01		Nakanishi, Naruhiko et al.	<input checked="" type="checkbox"/>				
47	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6614642	20030902	14	Capacitor over plug structure	361/306.1	257/308; 361/309		Moon, Bum-ki et al.	<input checked="" type="checkbox"/>				
48	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6603161	20030805	58	Semiconductor device having ferroelectric ca	257/295	257/308; 257/311;		Kanaya, Hiroyuki et al.	<input checked="" type="checkbox"/>				
49	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6600185	20030729	34	Ferroelectric capacitor with dielectric lining	257/296	257/295; 257/316		Tani, Kouichi et al.	<input checked="" type="checkbox"/>				
50	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6583463	20030624	60	Semiconductor integrated circuit devi	257/306			Nakanishi, Naruhiko et al.	<input checked="" type="checkbox"/>				
51	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6534780	20030318	13	Array of ultra-small pores for memory cells	257/3	257/528; 257/529;		Gonzalez, Fernando et al.	<input checked="" type="checkbox"/>				
52	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6486531	20021126	12	Contact structure with a lower interconnection	257/532	257/534; 257/775		Oh, Jae-hee	<input checked="" type="checkbox"/>				
53	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6473331	20021029	275	Semiconductor memory device and various svst	365/145	257/E27.10; 4;		Takashima, Daisaburo	<input checked="" type="checkbox"/>				
54	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6448597	20020910	19	DRAM having a stacked capacitor and a method	257/295	257/296;		Kasai, Naoki et al.	<input checked="" type="checkbox"/>				
55	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6399974	20020604	18	Semiconductor memory device using an insulat	257/295	257/298; 257/306;		Ohtsuki, Sumito	<input checked="" type="checkbox"/>				

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